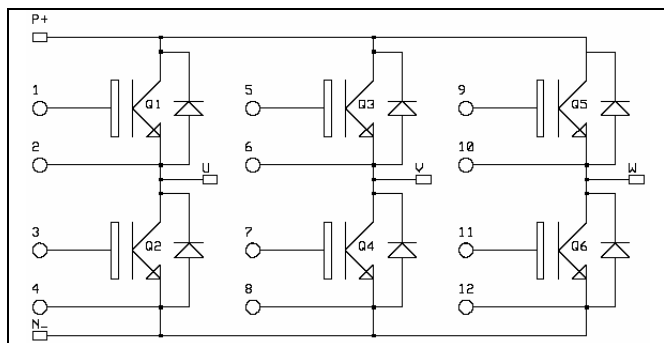
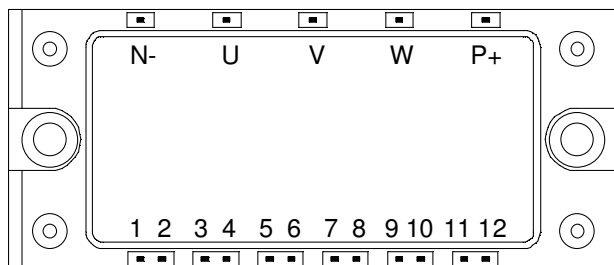


**3 Phase bridge
NPT IGBT Power Module**

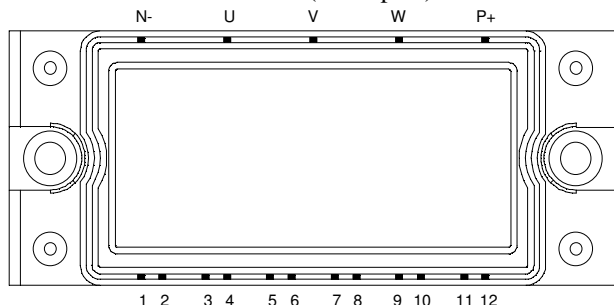
**$V_{CES} = 1200V$
 $I_C = 25A @ T_c = 80^\circ C$**



Pin out: APTGF25X120E2 (Long pins)



Pin out: APTGF25X120P2 (Short pins)



Application

- AC Motor control

Features

- Non Punch Through (NPT) IGBT®
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	A
		$T_C = 80^\circ C$	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	70
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	200
SCSOA	Short circuit Safe Operating Area	$T_j = 150^\circ C$	250A@1200V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 500\mu A$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 1200V$	$T_j = 25^\circ C$ $T_j = 125^\circ C$	0.5 2	0.8	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 25A$	$T_j = 25^\circ C$ $T_j = 125^\circ C$	2.5 3.1	3.0 3.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	4.5	5.5	6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			180	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		1650		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		250		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		110		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($125^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 25A$ $R_G = 47\Omega$		75	150	ns
T_r	Rise Time			65	130	
$T_{d(off)}$	Turn-off Delay Time			400	600	
T_f	Fall Time			50	100	

Reverse diode ratings and characteristics

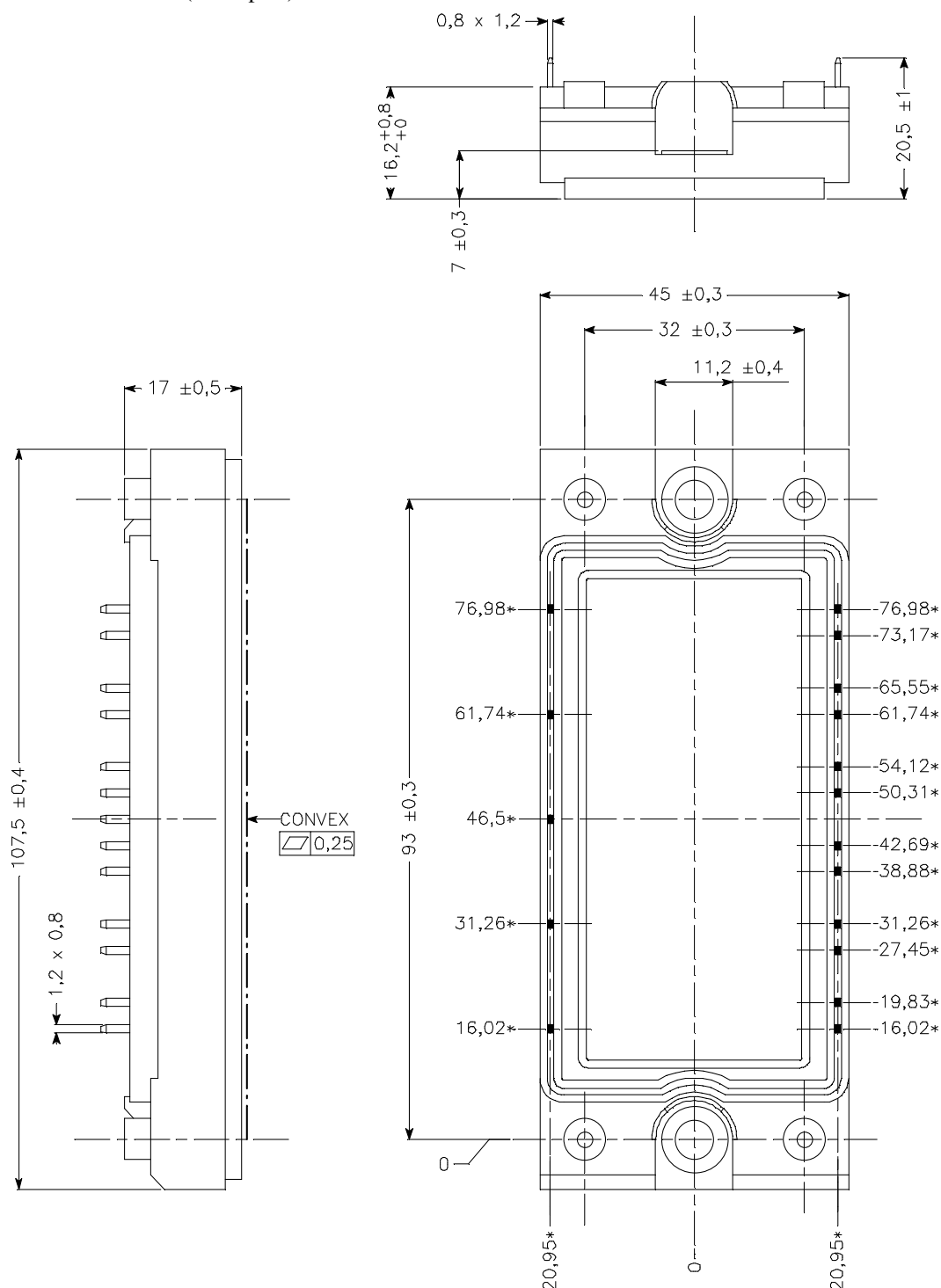
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 25A$ $V_{GE} = 0V$	$T_j = 25^\circ C$ $T_j = 125^\circ C$	2.3 1.8	2.8	V
t_{rr}	Reverse Recovery Time	$I_F = 25A$ $V_R = 600V$ $di/dt = 800A/\mu s$	$T_j = 125^\circ C$	0.13		μs
Q_{rr}	Reverse Recovery Charge	$I_F = 25A$ $V_R = 600V$ $di/dt = 800A/\mu s$	$T_j = 25^\circ C$ $T_j = 125^\circ C$	2.3 6		μC

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case		IGBT			0.6	°C/W
			Diode			1	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	2		3.5	N.m
Wt	Package Weight					185	g

Package outline

Pin out: APTGF25X120P2 (Short pins)



ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS : $\pm 0,4$

APT reserves the right to change, without notice, the specifications and information contained herein

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